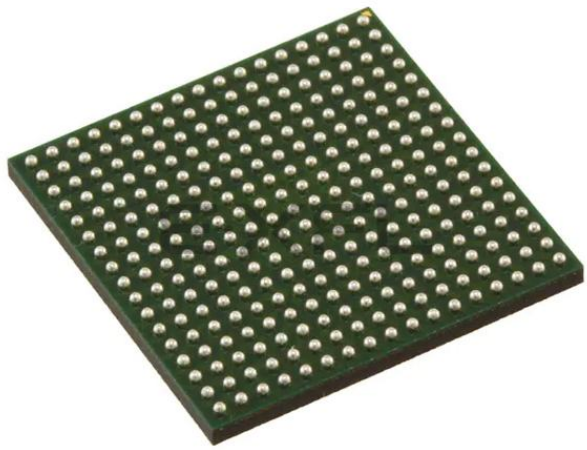

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	792
Total RAM Bits	-
Number of I/O	120
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	289-TFBGA, CSBGA
Supplier Device Package	289-CSP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp030v2-cs289i

Table of Contents

Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-21 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings

I/O Standard	Drive Strength	Equiv. Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	IOL[1]	IOH[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VDD 3 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4,5]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *Note that 1.2 V LVCMOS and 3.3 V LVCMOS wide range are applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
3. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to IGLOO PLUS V2 devices operating at $VCC_I \geq VCC$.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-25 • Summary of I/O Timing Characteristics—Software Default Settings, STD Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.97	1.76	0.18	0.85	1.15	0.66	1.80	1.39	2.20	2.64	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	5 pF	–	0.97	2.47	0.18	1.18	1.64	0.66	2.48	1.91	3.16	3.76	ns
2.5 V LVCMOS	12 mA	12 mA	High	5 pF	–	0.97	1.77	0.18	1.06	1.22	0.66	1.81	1.51	2.22	2.56	ns
1.8 V LVCMOS	8 mA	8 mA	High	5 pF	–	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns
1.5 V LVCMOS	4 mA	4 mA	High	5 pF	–	0.97	2.29	0.18	1.16	1.62	0.66	2.33	2.00	2.37	2.57	ns

Notes:

1. *Note that 3.3 V LVCMOS wide range is applicable to 100 µA drive strength only. The configuration will not operate at the equivalent software default drive strength. These values are for normal ranges only.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-58 • Minimum and Maximum DC Input and Output Levels

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.7 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
3. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

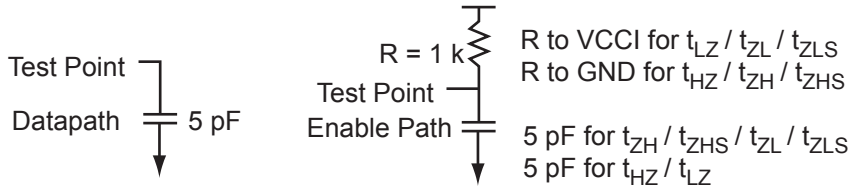


Figure 2-10 • AC Loading

Table 2-59 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.5	0.75	5

*Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

***Table 2-73* • Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-13 on page 2-43 for more information.*

1.2 V DC Core Voltage

Table 2-75 • Input Data Register Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.66	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.43	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.86	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.86	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

Output Enable Register

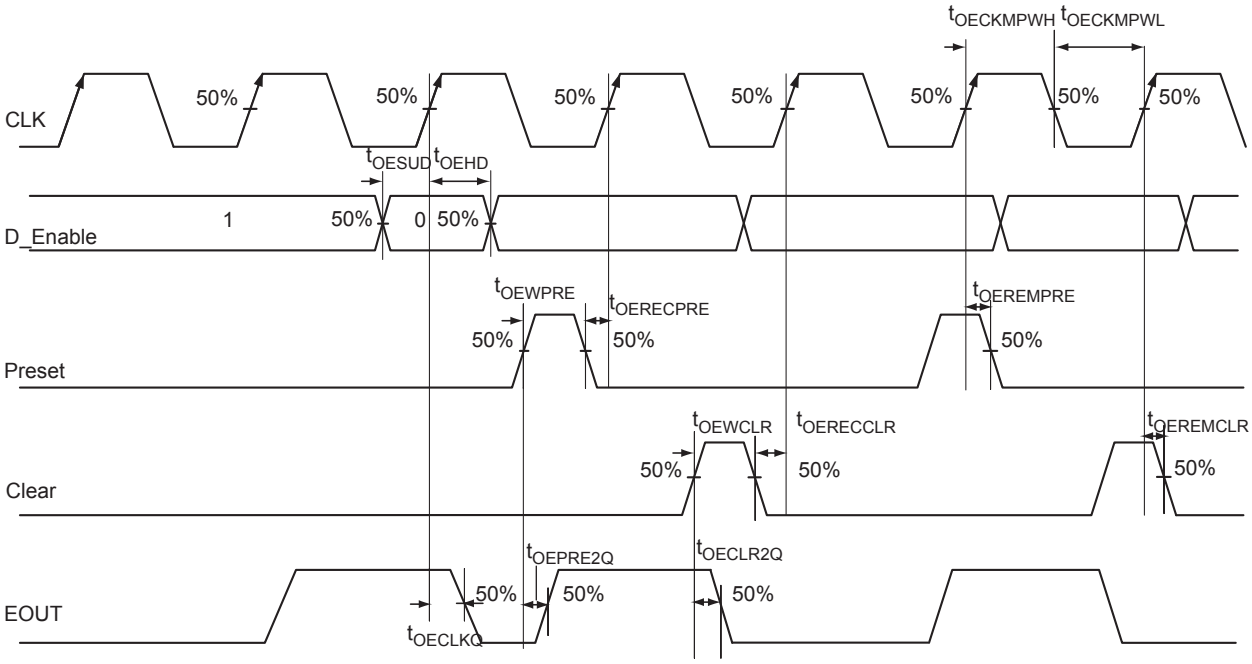


Figure 2-16 • **Output Enable Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-78 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.68	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.33	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.84	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.91	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The IGLOO PLUS library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/ E Macro Library Guide*.

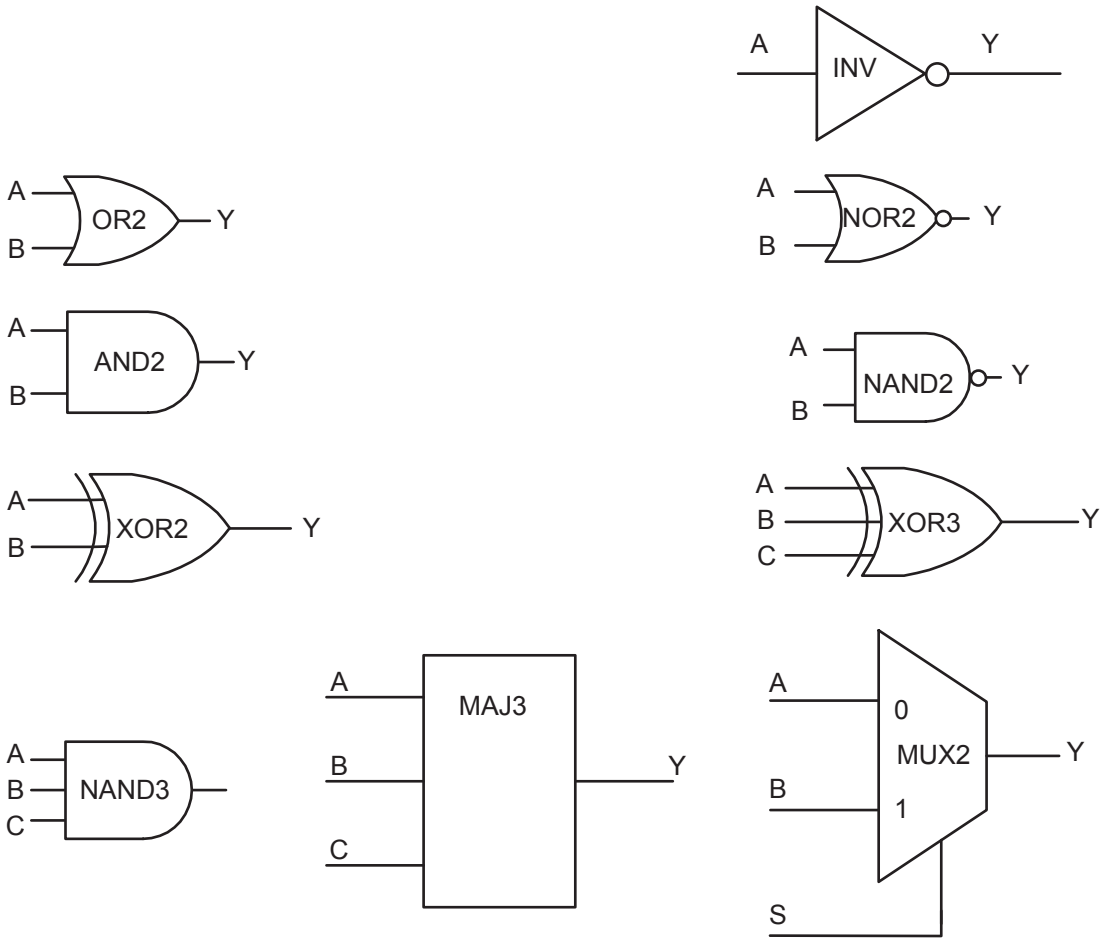
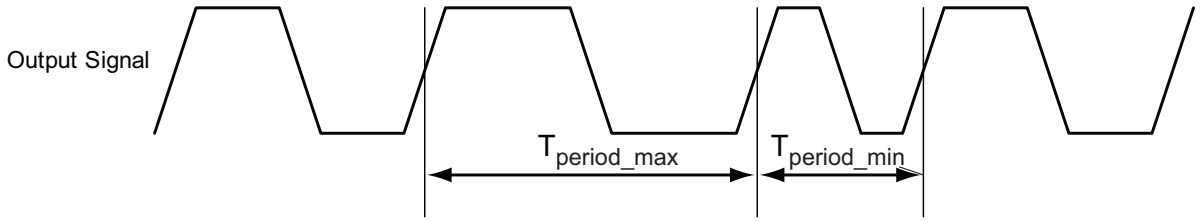


Figure 2-17 • **Sample of Combinatorial Cells**



Note: Peak-to-peak jitter measurements are defined by $T_{peak\text{-}to\text{-}peak} = T_{period\_max} - T_{period\_min}$.

Figure 2-22 • **Peak-to-Peak Jitter Definition**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-92 • RAM4K9
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.68	ns
t_{ENH}	REN, WEN hold time	0.13	ns
t_{BKS}	BLK setup time	1.37	ns
t_{BKH}	BLK hold time	0.13	ns
t_{DS}	Input data (DIN) setup time	0.59	ns
t_{DH}	Input data (DIN) hold time	0.30	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.94	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	2.55	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.51	ns
t_{C2CWWL} [1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.29	ns
t_{C2CRWH} [1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.24	ns
t_{C2CWRH} [1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.40	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	1.72	ns
	RESET Low to data out Low on DOUT (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-93 • RAM512X18
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.69	ns
t_{AH}	Address hold time	0.13	ns
t_{ENS}	REN, WEN setup time	0.61	ns
t_{ENH}	REN, WEN hold time	0.07	ns
t_{DS}	Input data (WD) setup time	0.59	ns
t_{DH}	Input data (WD) hold time	0.30	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	3.51	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.43	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.21	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.25	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	1.72	ns
	RESET Low to data out Low on RD (pipelined)	1.72	ns
$t_{REMRSTB}$	RESET removal	0.51	ns
$t_{RECRSTB}$	RESET recovery	2.68	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

1.2 V DC Core Voltage

***Table 2-94* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.25	ns
t_{ENH}	REN, WEN hold time	0.25	ns
t_{BKS}	BLK setup time	2.54	ns
t_{BKH}	BLK hold time	0.25	ns
t_{DS}	Input data (DIN) setup time	1.10	ns
t_{DH}	Input data (DIN) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	2.82	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.32	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.21	ns
	RESET Low to data out Low on DOUT (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

FIFO

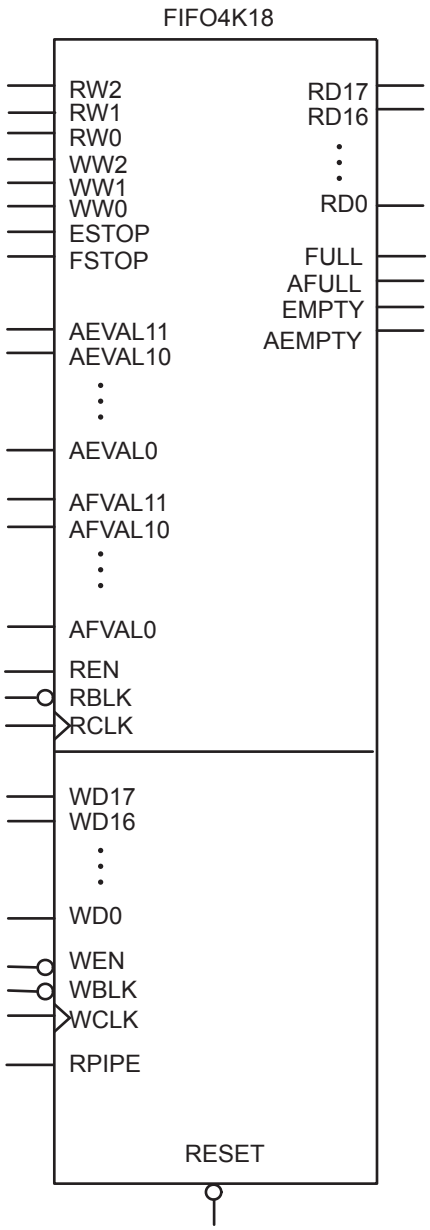


Figure 2-29 • **FIFO Model**

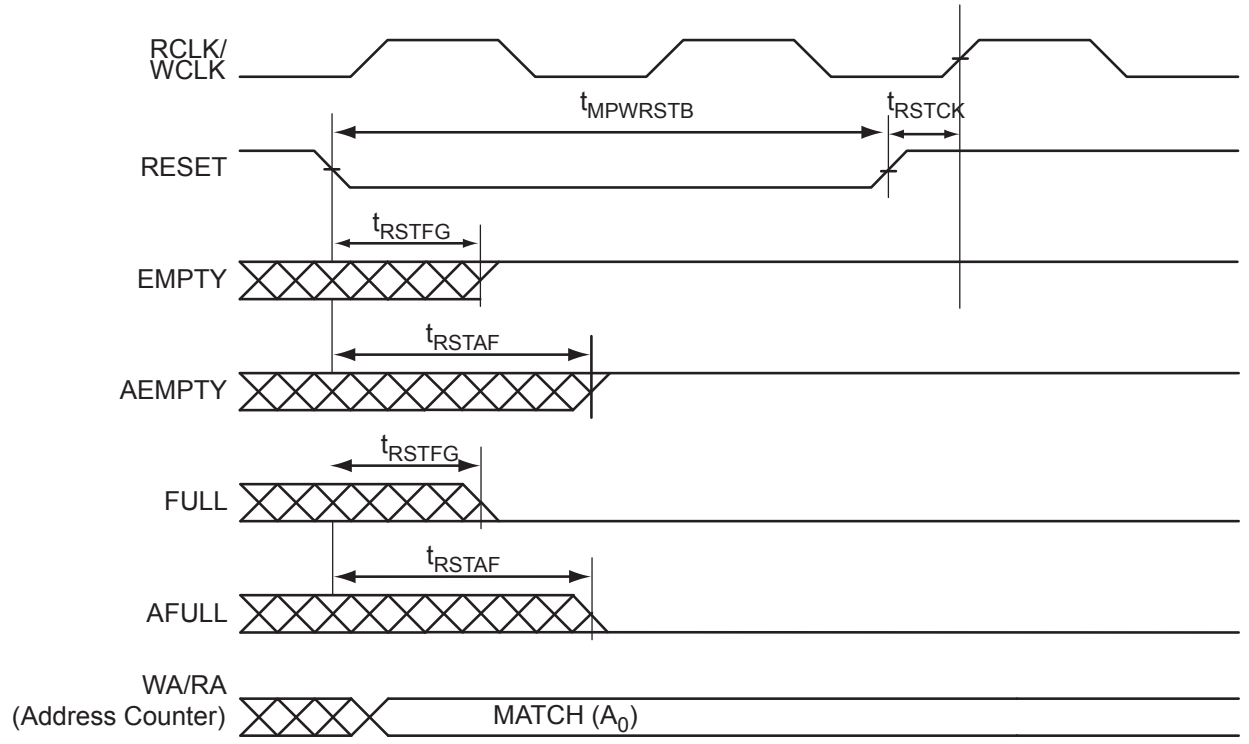


***Figure 2-32* • FIFO Reset**

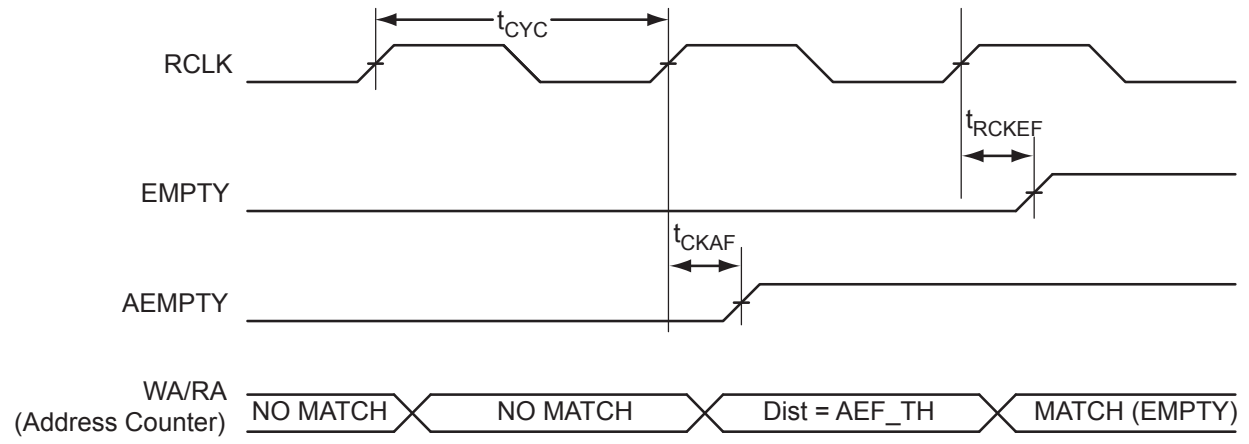


***Figure 2-33* • FIFO EMPTY Flag and AEMPTY Flag Assertion**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-96 • FIFO

Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.66	ns
t_{ENH}	REN, WEN Hold Time	0.13	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.63	ns
t_{DH}	Input Data (WD) Hold Time	0.20	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.77	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.50	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.94	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.79	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	10.71	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.90	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.68	ns
	RESET Low to Data Out Low on RD (pipelined)	1.68	ns
$t_{REMRSTB}$	RESET Removal	0.51	ns
$t_{RECRSTB}$	RESET Recovery	2.68	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Special Function Pins

NC **No Connect**

This pin is not connected to circuitry within the device. These pins can be driven to any voltage or can be left floating with no effect on the operation of the device.

DC **Do Not Connect**

This pin should not be connected to any signals on the PCB. These pins should be left unconnected.

Packaging

Semiconductor technology is constantly shrinking in size while growing in capability and functional integration. To enable next-generation silicon technologies, semiconductor packages have also evolved to provide improved performance and flexibility.

Microsemi consistently delivers packages that provide the necessary mechanical and environmental protection to ensure consistent reliability and performance. Microsemi IC packaging technology efficiently supports high-density FPGAs with large-pin-count Ball Grid Arrays (BGAs), but is also flexible enough to accommodate stringent form factor requirements for Chip Scale Packaging (CSP). In addition, Microsemi offers a variety of packages designed to meet your most demanding application and economic requirements for today's embedded and mobile systems.

Related Documents

IGLOO PLUS Device Family User's Guide

http://www.microsemi.com/soc/documents/IGLOOPLUS_UG.pdf

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

http://www.microsemi.com/soc/documents/PckgMechDrwngs.pdf

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials are available at
http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

VQ128	
Pin Number	**AGLP030 Function**
106	IO26RSB0
107	IO25RSB0
108	IO23RSB0
109	IO22RSB0
110	IO21RSB0
111	IO19RSB0
112	IO18RSB0
113	VCC
114	IO17RSB0
115	IO16RSB0
116	IO14RSB0
117	IO13RSB0
118	IO12RSB0
119	IO10RSB0
120	IO09RSB0
121	VCCIB0
122	GND
123	IO07RSB0
124	IO05RSB0
125	IO03RSB0
126	IO02RSB0
127	IO01RSB0
128	IO00RSB0

CS289	
Pin Number	**AGLP060 Function**
P8	GND
P9	IO91RSB2
P10	IO86RSB2
P11	IO81RSB2
P12	NC
P13	VCCIB2
P14	NC
P15	GDA2/IO78RSB2
P16	GDC2/IO80RSB2
P17	VJTAG
R1	GND
R2	GEA2/IO110RSB2
R3	NC
R4	NC
R5	NC
R6	VCCIB2
R7	IO102RSB2
R8	IO97RSB2
R9	IO93RSB2
R10	IO89RSB2
R11	GND
R12	NC
R13	NC
R14	NC
R15	NC
R16	TMS
R17	TRST
T1	GEA1/IO112RSB3
T2	GEC2/IO108RSB2
T3	NC
T4	GND
T5	NC
T6	IO103RSB2
T7	IO100RSB2
T8	IO95RSB2
T9	VCCIB2
T10	IO88RSB2
T11	IO84RSB2

CS289	
Pin Number	**AGLP060 Function**
T12	IO82RSB2
T13	NC
T14	GND
T15	NC
T16	TDI
T17	TDO
U1	FF/GEB2/IO109RSB2
U2	GND
U3	NC
U4	IO107RSB2
U5	IO105RSB2
U6	IO101RSB2
U7	GND
U8	IO94RSB2
U9	IO92RSB2
U10	IO87RSB2
U11	IO85RSB2
U12	GND
U13	NC
U14	NC
U15	NC
U16	TCK
U17	VPUMP

CS289	
Pin Number	**AGLP125 Function**
P8	GND
P9	IO132RSB2
P10	IO125RSB2
P11	IO126RSB2
P12	IO112RSB2
P13	VCCIB2
P14	IO108RSB2
P15	GDA2/IO105RSB2
P16	GDC2/IO107RSB2
P17	VJTAG
R1	GND
R2	GEA2/IO164RSB2
R3	IO158RSB2
R4	IO155RSB2
R5	IO150RSB2
R6	VCCIB2
R7	IO145RSB2
R8	IO141RSB2
R9	IO134RSB2
R10	IO130RSB2
R11	GND
R12	IO118RSB2
R13	IO116RSB2
R14	IO114RSB2
R15	IO110RSB2
R16	TMS
R17	TRST
T1	GEA1/IO166RSB3
T2	GEC2/IO162RSB2
T3	IO153RSB2
T4	GND
T5	IO147RSB2
T6	IO143RSB2
T7	IO140RSB2
T8	IO139RSB2
T9	VCCIB2
T10	IO131RSB2
T11	IO127RSB2

CS289	
Pin Number	**AGLP125 Function**
T12	IO124RSB2
T13	IO122RSB2
T14	GND
T15	IO115RSB2
T16	TDI
T17	TDO
U1	FF/GEB2/IO163RSB2
U2	GND
U3	IO151RSB2
U4	IO149RSB2
U5	IO146RSB2
U6	IO142RSB2
U7	GND
U8	IO138RSB2
U9	IO136RSB2
U10	IO133RSB2
U11	IO129RSB2
U12	GND
U13	IO123RSB2
U14	IO120RSB2
U15	IO117RSB2
U16	TCK
U17	VPUMP

Revision	Changes	Page
Revision 13 (June 2012)	Figure 2-30 • FIFO Read and Figure 2-31 • FIFO Write have been added (SAR 34843).	2-73
	Updated the terminology used in Timing Characteristics in the following tables: Table 2-96 • FIFO and Table 2-97 • FIFO (SAR 38236).	2-76
	The following sentence was removed from the "VMVx I/O Supply Voltage (quiet)" section in the "Pin Descriptions and Packaging" section: "Within the package, the VMV plane is decoupled from the simultaneous switching noise originating from the output buffer VCCI domain" and replaced with “Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks” (SAR 38320). The datasheet mentions that "VMV pins must be connected to the corresponding VCCI pins" for an ESD enhancement.	3-1
Revision 12 (March 2012)	The "In-System Programming (ISP) and Security" section and "Security" section were revised to clarify that although no existing security measures can give an absolute guarantee, Microsemi FPGAs implement the best security available in the industry (SAR 34664).	I, 1-2
	The Y security option and Licensed DPA Logo were added to the "IGLOO PLUS Ordering Information" section. The trademarked Licensed DPA Logo identifies that a product is covered by a DPA counter-measures license from Cryptography Research (SAR 34724).	III
	The "Specifying I/O States During Programming" section is new (SAR 34695).	1-7
	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO PLUS devices via an IEEE 1532 JTAG interface" (SAR 34684).	1-3